Appln. No.: 10/828,654

Amendment Dated April 13, 2006

Reply to Office Action of August 9, 2005

<u>Amendments to the Claims:</u> This listing of claims will replace all prior versions, and listings, of claims in the application

Listing of Claims:

1-9. (Canceled)

10. (Previously Presented) An apparatus for the generation of high-energy terahertz radiation comprising:

a source effective to produce optical radiation; and

a semiconductor substrate having a refractive index, n, and a photo-generated dipole generated upon interaction with the optical radiation, the photo-generated dipole oriented to radiate terahertz radiation having power at least about n² times higher than the power of the terahertz radiation radiated by a photo-generated dipole which is not so oriented; and

a structure of a polytetrafluoroethylene base with an InAs film forming a grating on the surface of the semiconductor substrate.

- 11. (Original) The apparatus of claim 10 wherein the grating has an apex angle of about ninety degrees.
- 12. (Original) The apparatus of claim 10 wherein the InAs film has a thickness greater than the absorbance length of the optical radiation.
- 13: (Original) The apparatus of claim 10 wherein the optical radiation is incident substantially perpendicular to the grating of the semiconductor substrate.
- 14. (Currently Amended) The apparatus of claim 10 wherein the grating structure-includes a grating formed by a series of structures each having the configuration of a triangle.
- 15. (Original) The apparatus of claim 14 wherein the optical radiation is incident on the surface of the semiconductor substrate at the Brewster's angle to each individual structure of the grating.

16-20. (Canceled)